

N-channel 600 V, 0.35  $\Omega$  typ., 11 A  
MDmesh™ M2 Power MOSFETs in D<sup>2</sup>PAK and DPAK packages

Datasheet - production data

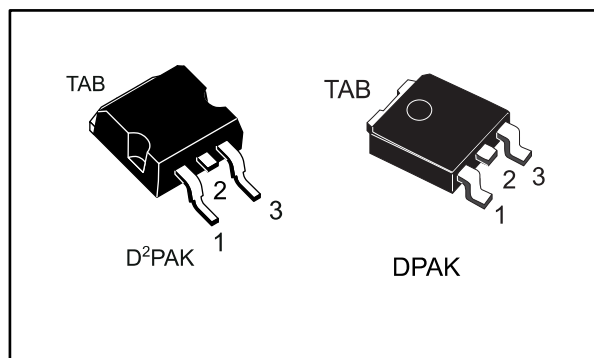
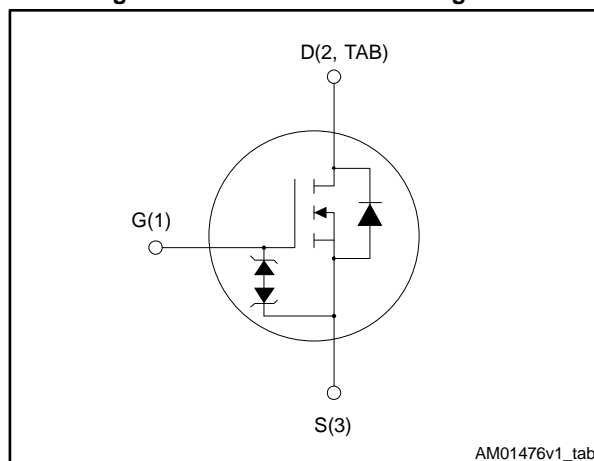


Figure 1: Internal schematic diagram



## Features

Order code	V <sub>DS@T<sub>JMAX</sub></sub>	R <sub>DS(on)</sub> max.	I <sub>D</sub>
STB13N60M2	650 V	0.38 $\Omega$	11 A
STD13N60M2			

- Extremely low gate charge
- Excellent output capacitance (C<sub>oss</sub>) profile
- 100% avalanche tested
- Zener-protected

## Applications

- Switching applications

## Description

These devices are N-channel Power MOSFETs developed using MDmesh™ M2 technology. Thanks to their strip layout and improved vertical structure, these devices exhibit low on-resistance and optimized switching characteristics, rendering them suitable for the most demanding high efficiency converters.

Table 1: Device summary

Order code	Marking	Package	Packing
STB13N60M2	13N60M2	D <sup>2</sup> PAK	Tape and reel
STD13N60M2		DPAK	

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# 1 Electrical ratings

**Table 2: Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{GS}$	Gate-source voltage	$\pm 25$	V
$I_D$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	11	A
$I_D$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	7	A
$I_{DM}^{(1)}$	Drain current (pulsed)	44	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	110	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	15	V/ns
$dv/dt^{(3)}$	MOSFET $dv/dt$ ruggedness	50	
$T_{stg}$	Storage temperature range	- 55 to 150	$^\circ\text{C}$
$T_j$	Operating junction temperature range		

**Notes:**

(1)Pulse width limited by safe operating area.

(2) $I_{SD} \leq 11\text{ A}$ ,  $di/dt \leq 400\text{ A}/\mu\text{s}$ ;  $V_{DS\text{ peak}} < V_{(BR)DSS}$ ,  $V_{DD} = 400\text{ V}$ .

(3) $V_{DS} \leq 480\text{ V}$ .

**Table 3: Thermal data**

Symbol	Parameter	Value		Unit
		D <sup>2</sup> PAK	DPAK	
$R_{thj\text{-case}}$	Thermal resistance junction-case max.	1.14		$^\circ\text{C}/\text{W}$
$R_{thj\text{-pcb}}^{(1)}$	Thermal resistance junction-pcb max.	30	50	

**Notes:**

(1)When mounted on FR-4 board of 1 inch<sup>2</sup>, 2 oz Cu.

**Table 4: Avalanche characteristics**

Symbol	Parameter	Value	Unit
$I_{AR}$	Avalanche current, repetitive or not repetitive (pulse width limited by $T_{j\text{max}}$ .)	2.8	A
$E_{AS}$	Single pulse avalanche energy (starting $T_j = 25\text{ }^\circ\text{C}$ , $I_D = I_{AR}$ ; $V_{DD} = 50\text{ V}$ )	125	mJ

## 2 Electrical characteristics

$T_C = 25\text{ °C}$  unless otherwise specified

**Table 5: On/off-states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$ , $I_D = 1\text{ mA}$	600			V
$I_{DSS}$	Zero-gate voltage drain current	$V_{GS} = 0\text{ V}$ , $V_{DS} = 600\text{ V}$			1	$\mu\text{A}$
		$V_{GS} = 0\text{ V}$ , $V_{DS} = 600\text{ V}$ , $T_C = 125\text{ °C}$ <sup>(1)</sup>			100	$\mu\text{A}$
$I_{GSS}$	Gate-body leakage current	$V_{DS} = 0\text{ V}$ , $V_{GS} = \pm 25\text{ V}$			$\pm 10$	$\mu\text{A}$
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$ , $I_D = 5.5\text{ A}$		0.35	0.38	$\Omega$

**Notes:**

<sup>(1)</sup>Defined by design, not subject to production test.

**Table 6: Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 100\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0\text{ V}$	-	580	-	pF
$C_{oss}$	Output capacitance		-	32	-	pF
$C_{rss}$	Reverse transfer capacitance		-	1.1	-	pF
$C_{oss\text{ eq.}}^{(1)}$	Equivalent output capacitance	$V_{DS} = 0\text{ to }480\text{ V}$ , $V_{GS} = 0\text{ V}$	-	120	-	pF
$R_G$	Intrinsic gate resistance	$f = 1\text{ MHz}$ , $I_D = 0\text{ A}$	-	6.6	-	$\Omega$
$Q_g$	Total gate charge	$V_{DD} = 480\text{ V}$ , $I_D = 11\text{ A}$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 17: "Test circuit for gate charge behavior"</a> )	-	17	-	nC
$Q_{gs}$	Gate-source charge		-	2.5	-	nC
$Q_{gd}$	Gate-drain charge		-	9	-	nC

**Notes:**

<sup>(1)</sup> $C_{oss\text{ eq.}}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$ .

Table 7: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 300\text{ V}$ , $I_D = 5.5\text{ A}$ , $R_G = 4.7\ \Omega$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 16: "Test circuit for resistive load switching times"</a> and <a href="#">Figure 21: "Switching time waveform"</a> )	-	11	-	ns
$t_r$	Rise time		-	10	-	ns
$t_{d(off)}$	Turn-off delay time		-	41	-	ns
$t_f$	Fall time		-	9.5	-	ns

Table 8: Source-drain diode

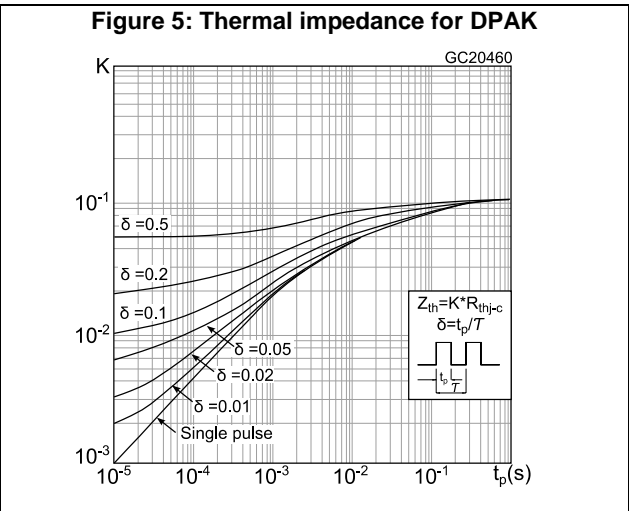
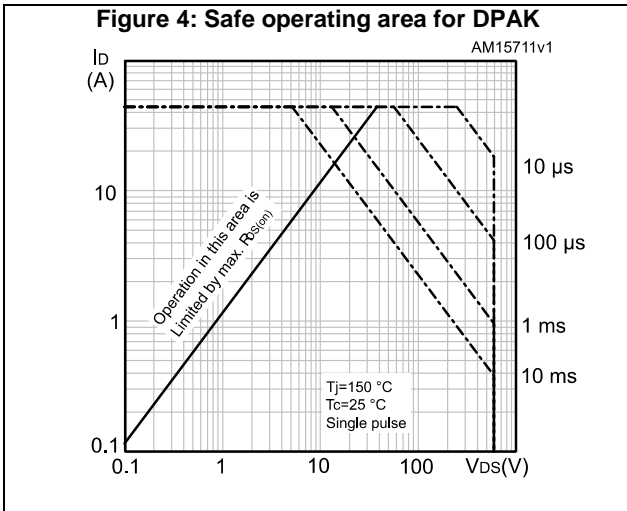
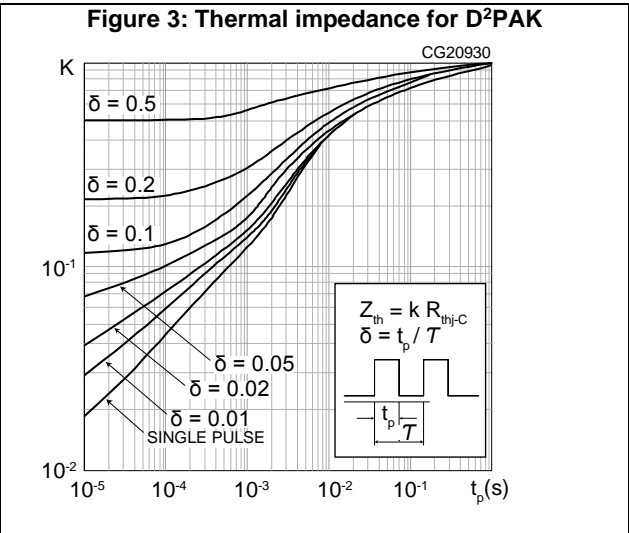
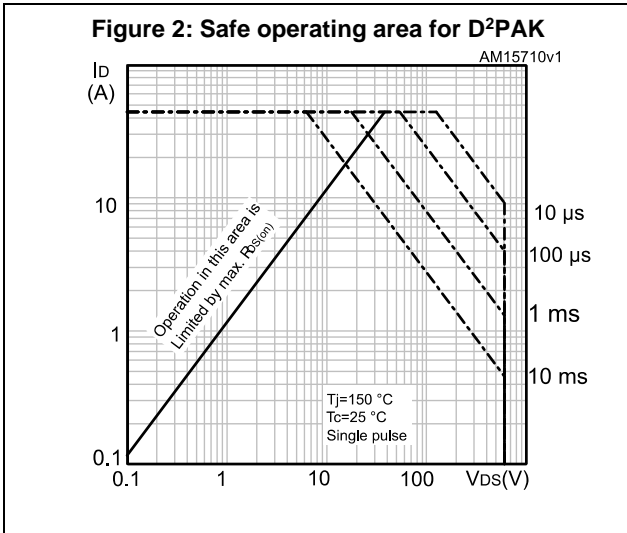
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		11	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		44	A
$V_{SD}^{(2)}$	Forward on voltage	$V_{GS} = 0\text{ V}$ , $I_{SD} = 11\text{ A}$	-		1.6	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 11\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 60\text{ V}$ (see <a href="#">Figure 18: "Test circuit for inductive load switching and diode recovery times"</a> )	-	297		ns
$Q_{rr}$	Reverse recovery charge		-	2.8		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	18.5		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 11\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 60\text{ V}$ , $T_j = 150\text{ }^\circ\text{C}$ (see <a href="#">Figure 18: "Test circuit for inductive load switching and diode recovery times"</a> )	-	394		ns
$Q_{rr}$	Reverse recovery charge		-	3.8		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	19		A

**Notes:**

(1) Pulse width is limited by safe operating area.

(2) Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%.

## 2.2 Electrical characteristics (curves)



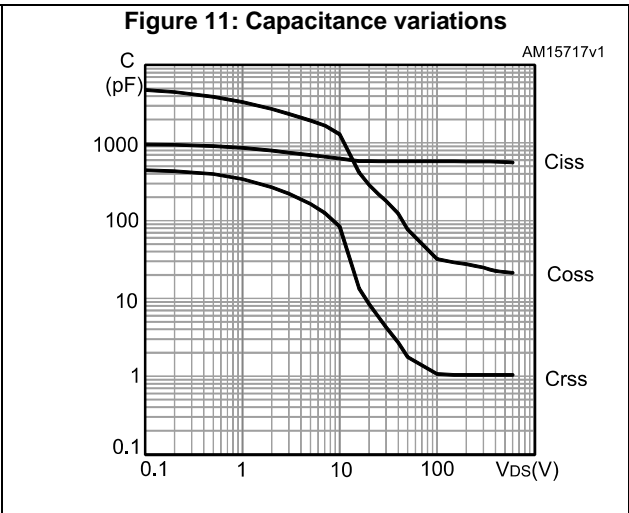
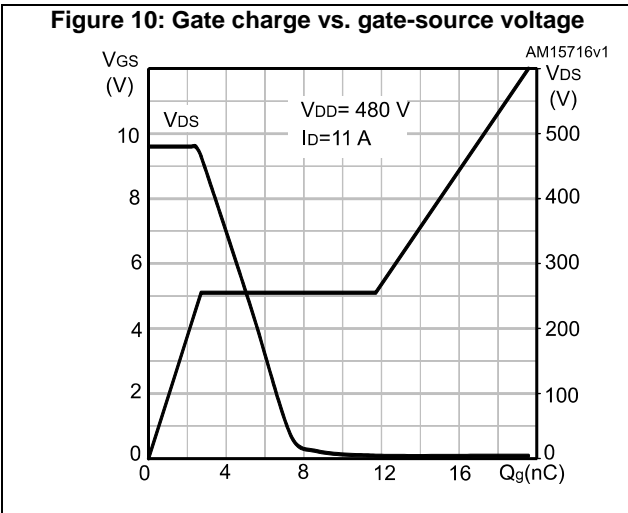
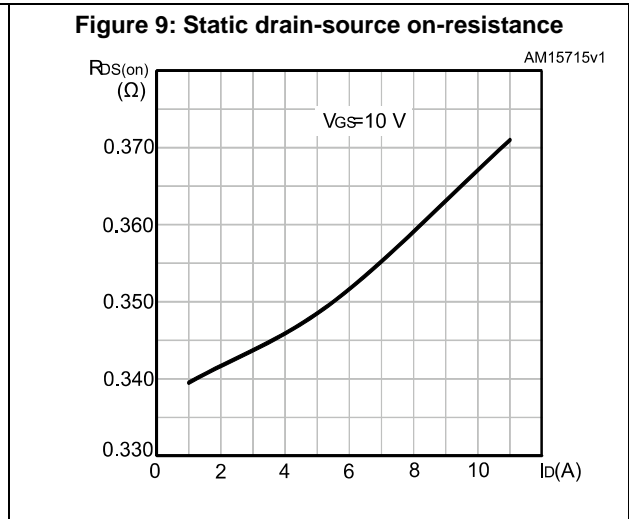
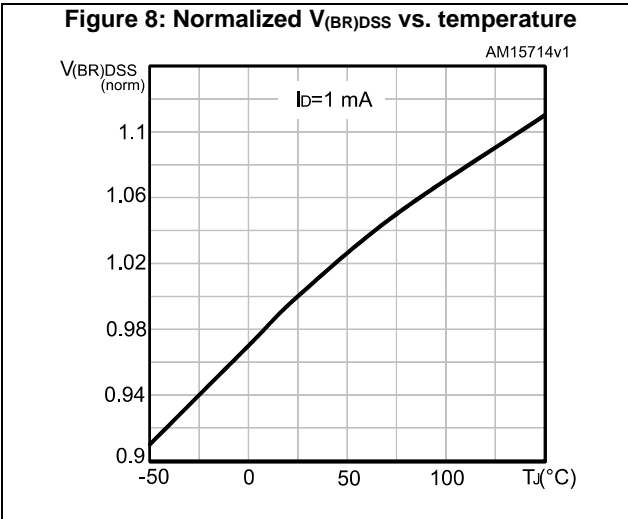
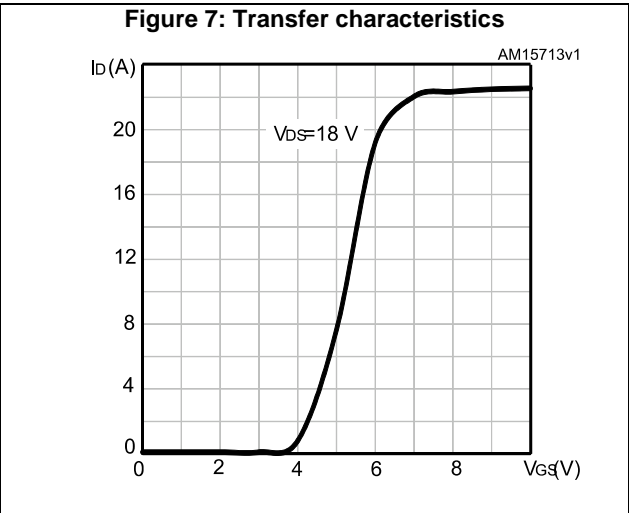
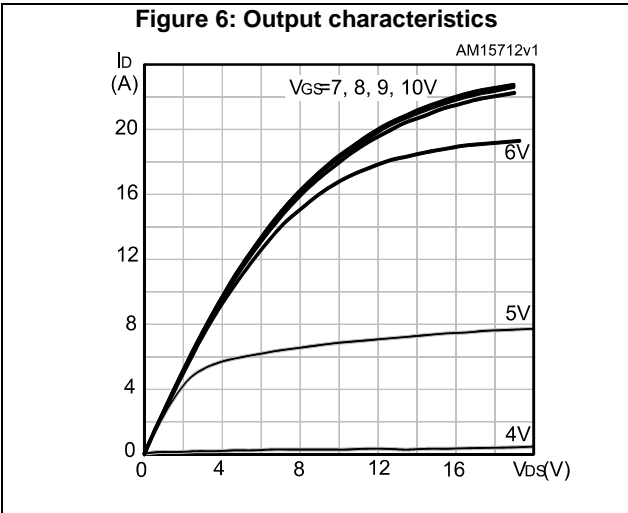


Figure 12: Normalized gate threshold voltage vs. temperature

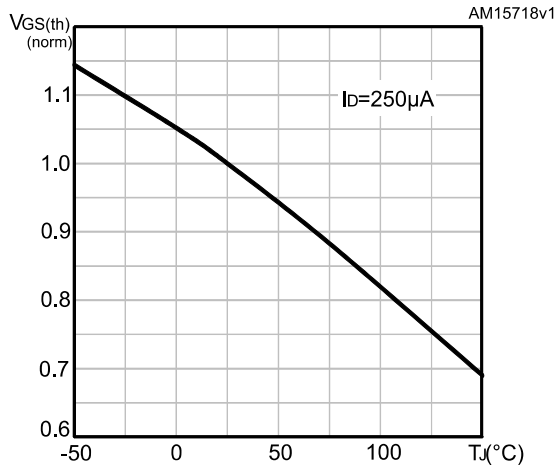


Figure 13: Normalized on-resistance vs. temperature

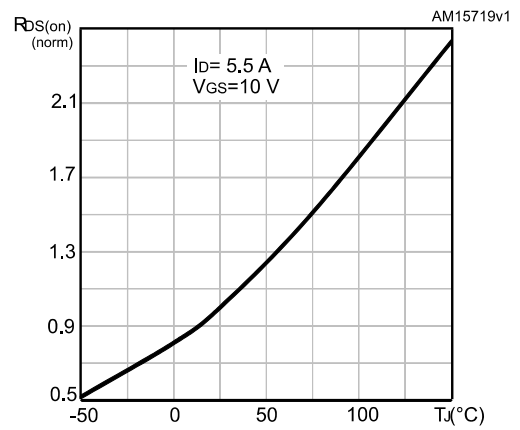


Figure 14: Source-drain diode forward characteristics

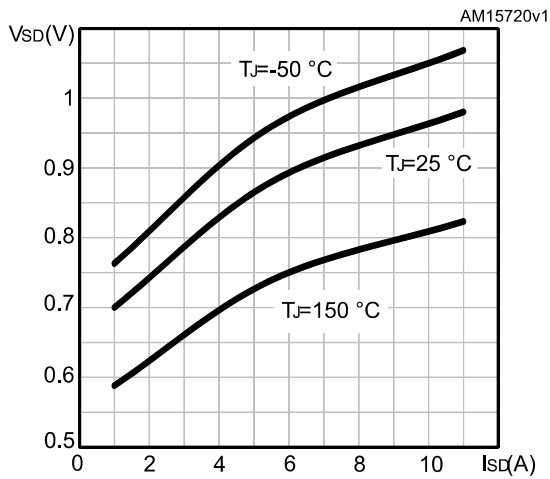
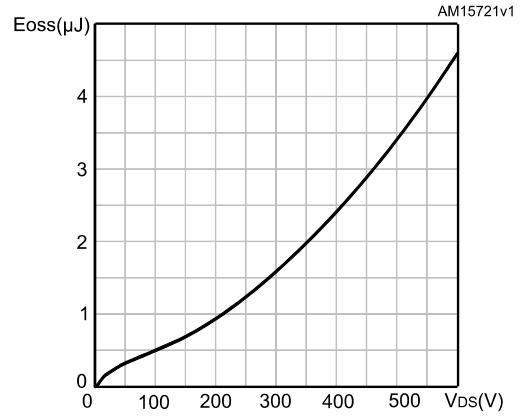


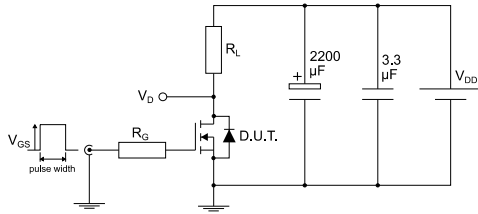
Figure 15: Output capacitance stored energy





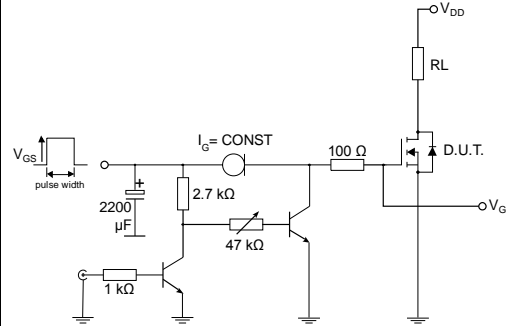
### 3 Test circuits

**Figure 16: Test circuit for resistive load switching times**



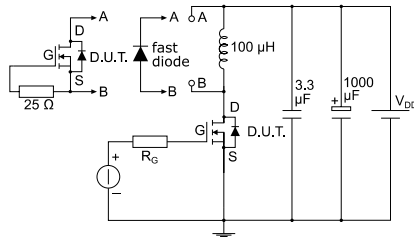
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**Figure 17: Test circuit for gate charge behavior**



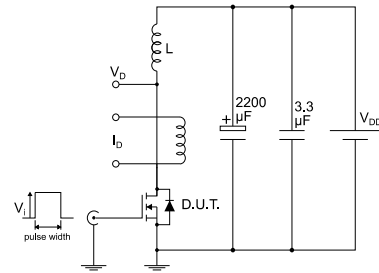
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**Figure 18: Test circuit for inductive load switching and diode recovery times**



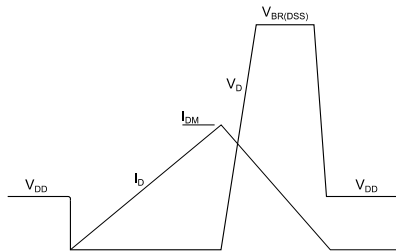
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**Figure 19: Unclamped inductive load test circuit**



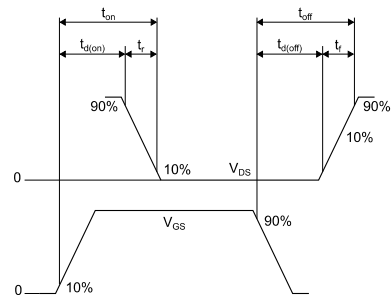
AM01471v1

**Figure 20: Unclamped inductive waveform**



AM01472v1

**Figure 21: Switching time waveform**



AM01473v1

## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK® is an ST trademark.

### 4.1 D<sup>2</sup>PAK (TO-263) type A package information

Figure 22: D<sup>2</sup>PAK (TO-263) type A package outline

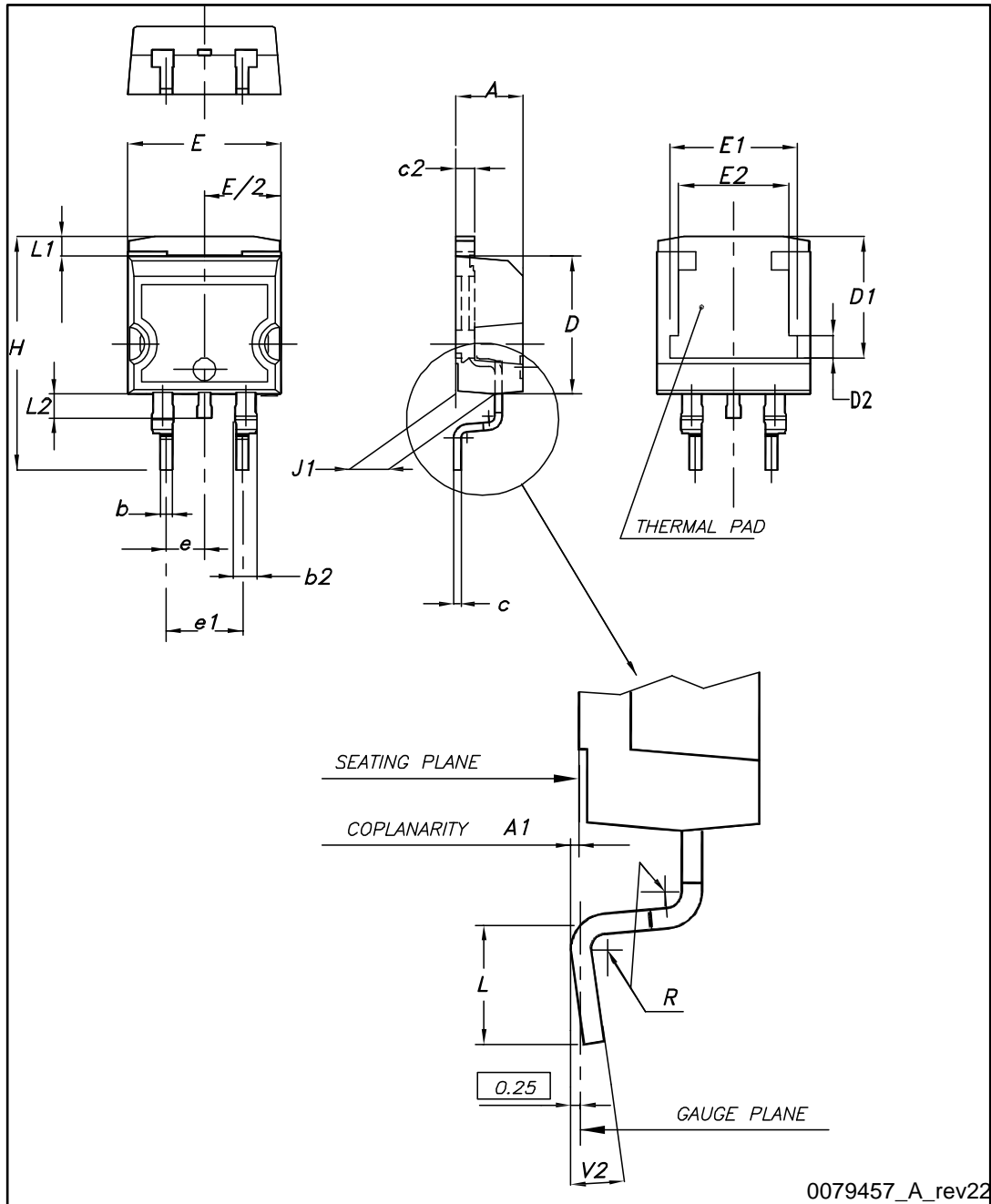
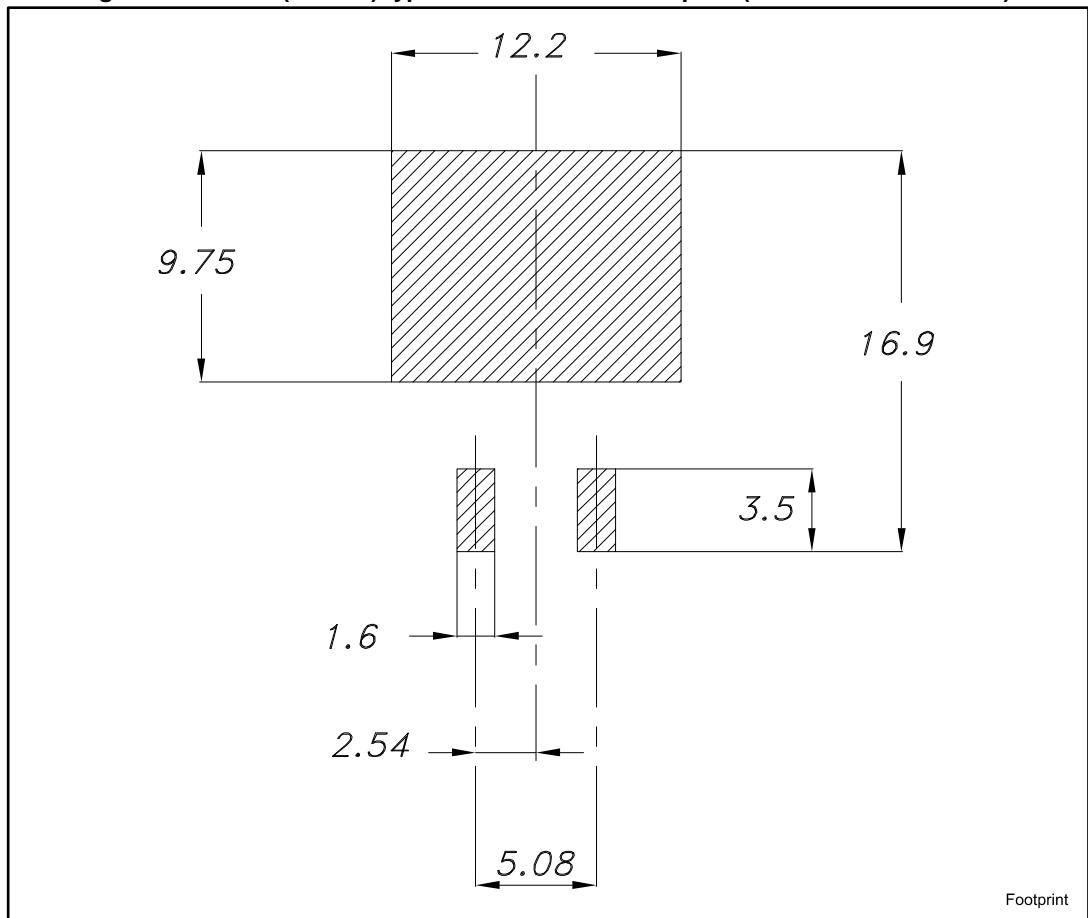


Table 9: D<sup>2</sup>PAK (TO-263) type A package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50	7.75	8.00
D2	1.10	1.30	1.50
E	10		10.40
E1	8.50	8.70	8.90
E2	6.85	7.05	7.25
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

Figure 23: D<sup>2</sup>PAK (TO-263) type A recommended footprint (dimensions are in mm)



### 4.2 DPAK (TO-252) type A2 package information

Figure 24: DPAK (TO-252) type A2 package outline

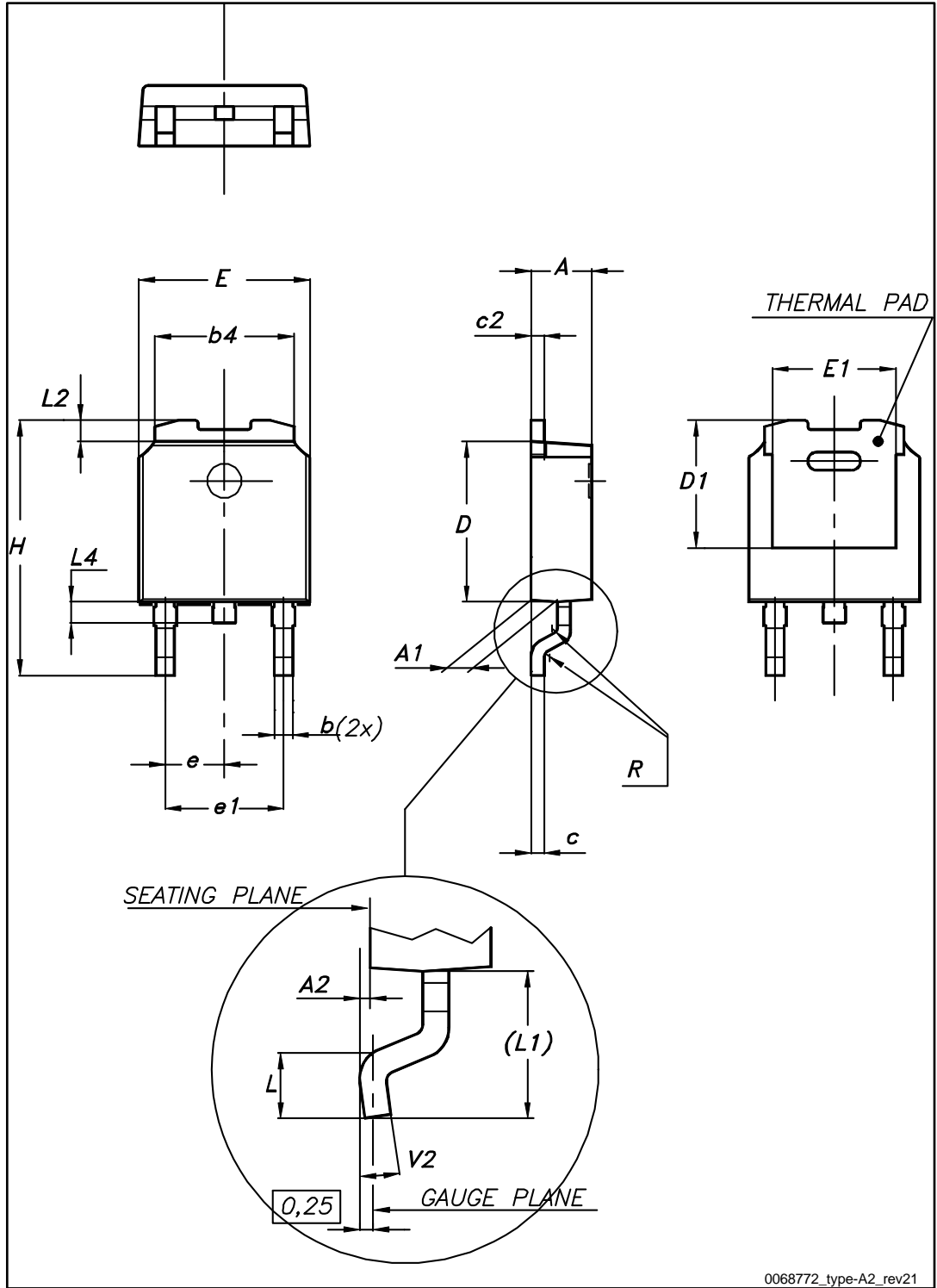
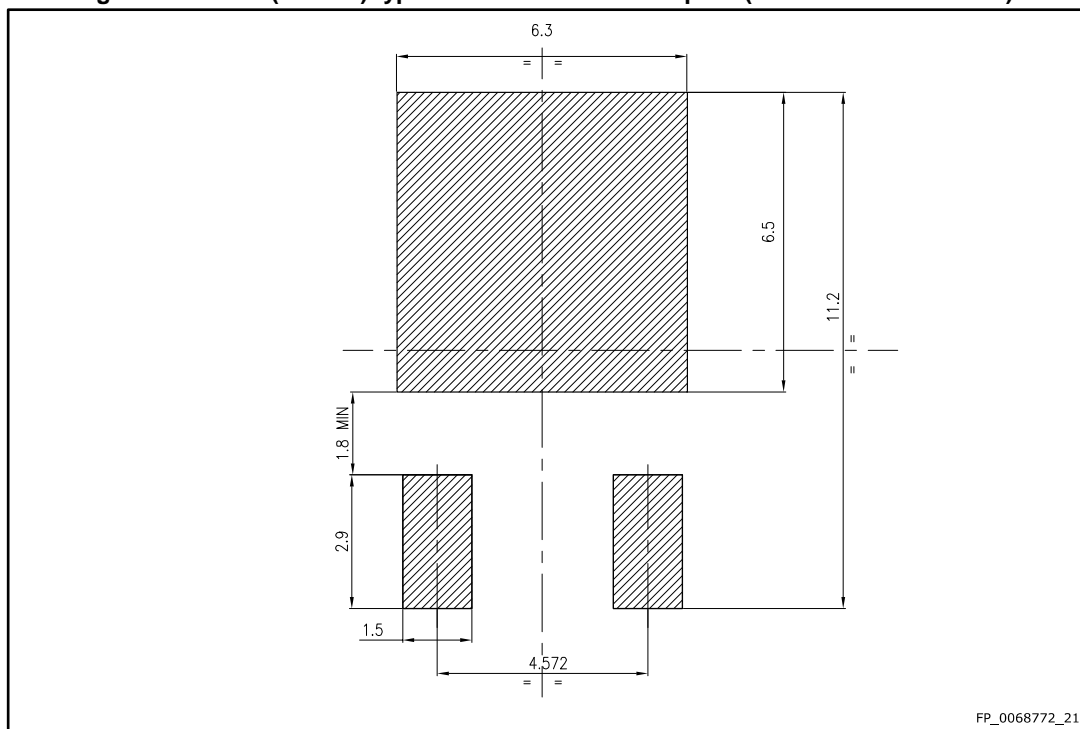


Table 10: DPAK (TO-252) type A2 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1	4.95	5.10	5.25
E	6.40		6.60
E1	5.10	5.20	5.30
e	2.16	2.28	2.40
e1	4.40		4.60
H	9.35		10.10
L	1.00		1.50
L1	2.60	2.80	3.00
L2	0.65	0.80	0.95
L4	0.60		1.00
R		0.20	
V2	0°		8°

Figure 25: DPAK (TO-252) type A2 recommended footprint (dimensions are in mm)



### 4.3 DPAK (TO-252) type C2 package information

Figure 26: DPAK (TO-252) type C2 package outline

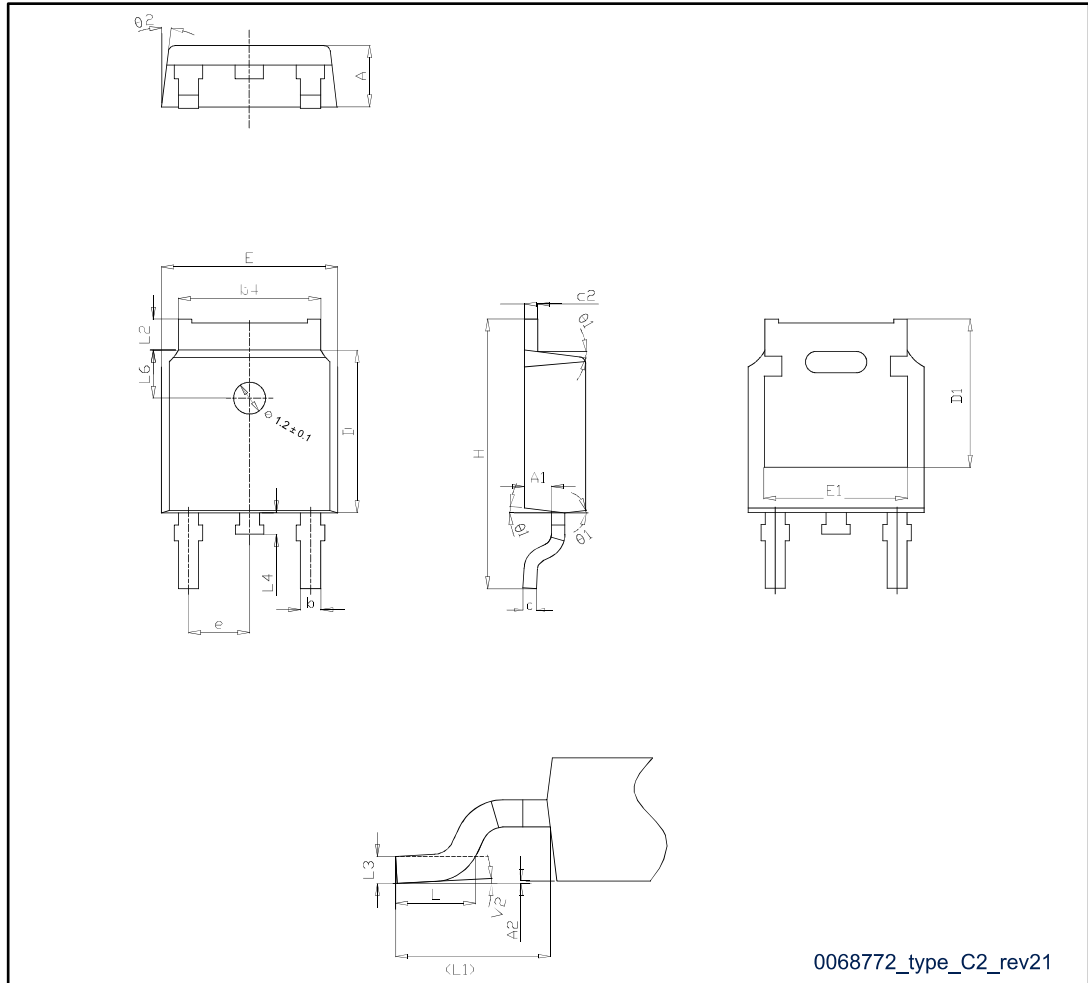
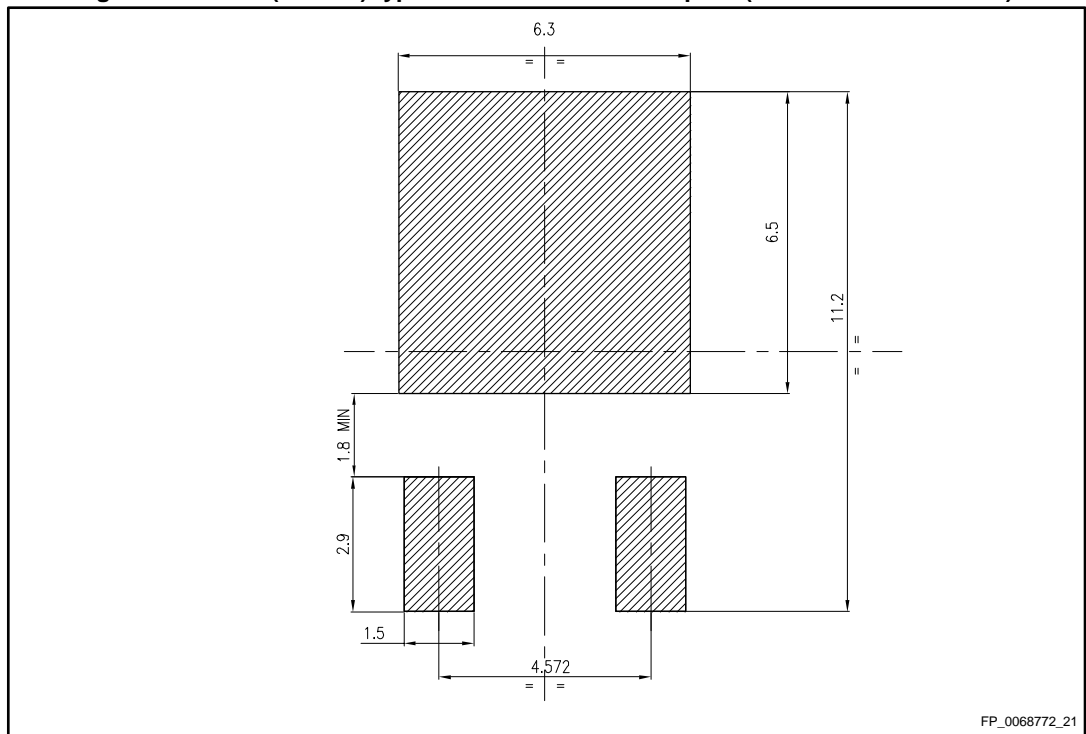




Table 11: DPAK (TO-252) type C2 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20	2.30	2.38
A1	0.90	1.01	1.10
A2	0.00		0.10
b	0.72		0.85
b4	5.13	5.33	5.46
c	0.47		0.60
c2	0.47		0.60
D	6.00	6.10	6.20
D1	5.10		5.60
E	6.50	6.60	6.70
E1	5.20		5.50
e	2.186	2.286	2.386
H	9.80	10.10	10.40
L	1.40	1.50	1.70
L1	2.90 REF		
L2	0.90		1.25
L3	0.51 BSC		
L4	0.60	0.80	1.00
L6	1.80 BSC		
θ1	5°	7°	9°
θ2	5°	7°	9°
V2	0°		8°

Figure 27: DPAK (TO-252) type C2 recommended footprint (dimensions are in mm)



### 4.4 D<sup>2</sup>PAK and DPAK packing information

Figure 28: Tape outline

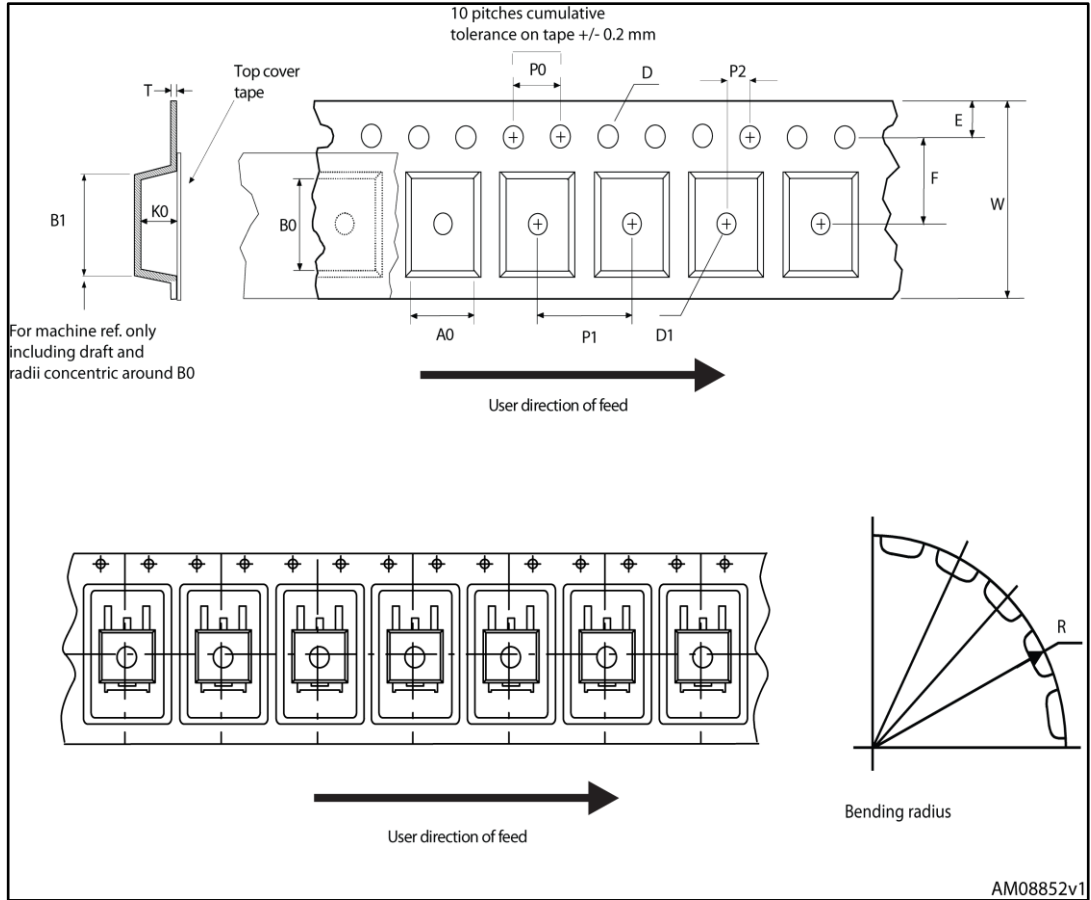


Figure 29: Reel outline

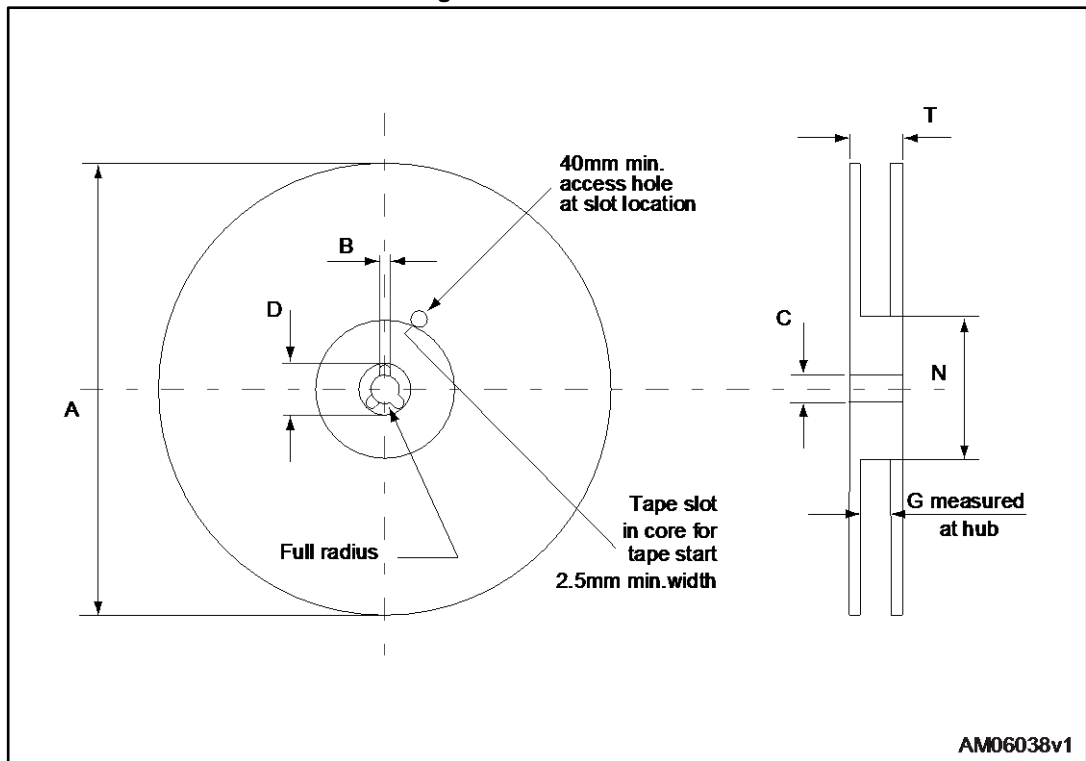


Table 12: D<sup>2</sup>PAK tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base quantity		1000
P2	1.9	2.1	Bulk quantity		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

Table 13: DPAK tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

## 5 Revision history

Table 14: Document revision history

Date	Revision	Changes
22-Apr-2013	1	First release.
28-Jun-2013	2	– Document status promoted from preliminary data to production data - Minor text changes
03-Mar-2014	3	– Updated: <i>Table 10</i> and <i>Table 25</i> - Minor text changes
12-Sep-2016	4	Updated the title, features and the description. Updated <a href="#">Section 4.1: "D2PAK (TO-263) type A package information"</a> , <a href="#">Section 4.2: "DPAK (TO-252) type A2 package information"</a> , <a href="#">Section 4.3: "DPAK (TO-252) type C2 package information"</a> and <a href="#">Section 4.4: "D2PAK and DPAK packing information"</a> .

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